CHINA BASE INTERNATIONAL

SOT-323

S8550W

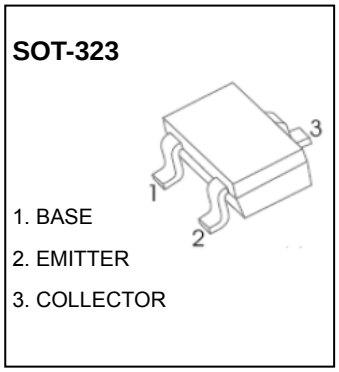
www.china-base.com.hk

TRANSISTOR (PNP)

FEATURES

Complimentary to S8050W

Collector current: I_C=0.5A



MARKING : 2TY

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.5	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

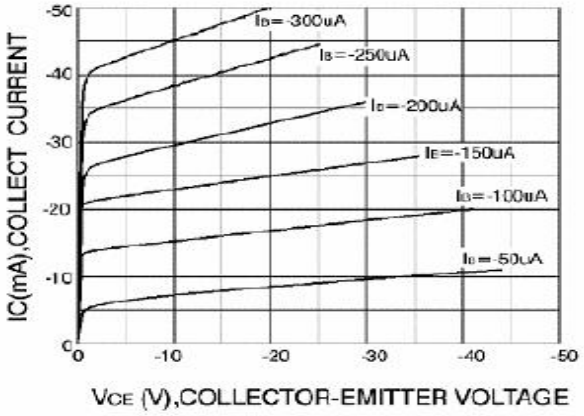
ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = -100μA, I_E=0	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C =-1mA, I_B=0	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}= -40V, I_E=0		-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -20V, I_B=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -3V, I_C=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= -1V, I_C= -50mA	120	400	
	$h_{FE(2)}$	V_{CE}= -1V, I_C= -500mA	50		
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-500mA, I_B= -50mA		-0.6	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-500mA, I_B= -50mA		-1.2	V
Transition frequency	f_T	V_{CE}= -6V, I_C= -20mA f=30MHz	150		MHz

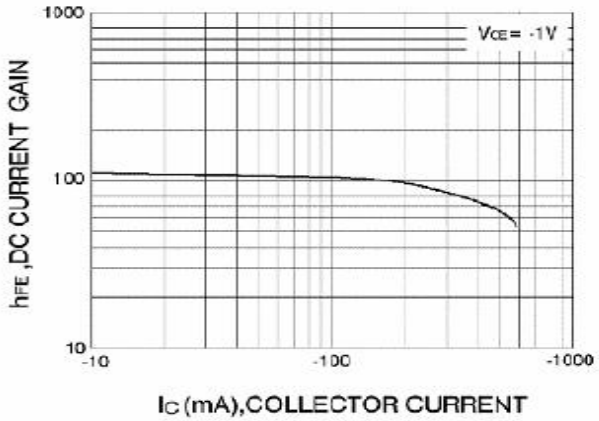
CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H	J
Range	120-200	200-350	300-400

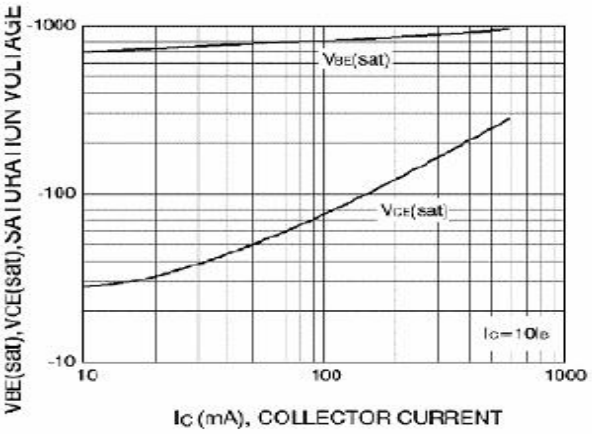
Typical Characteristics



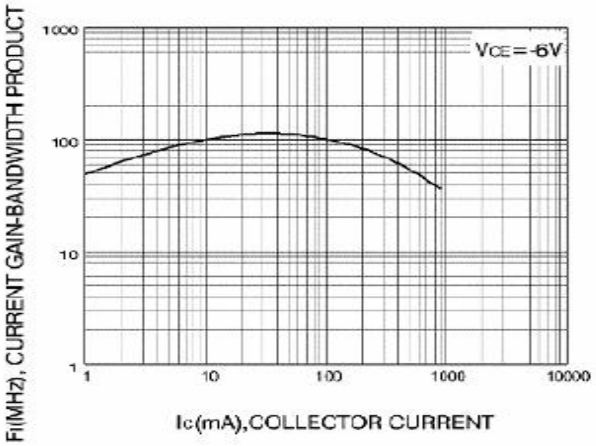
Static Characteristic



DC current Gain

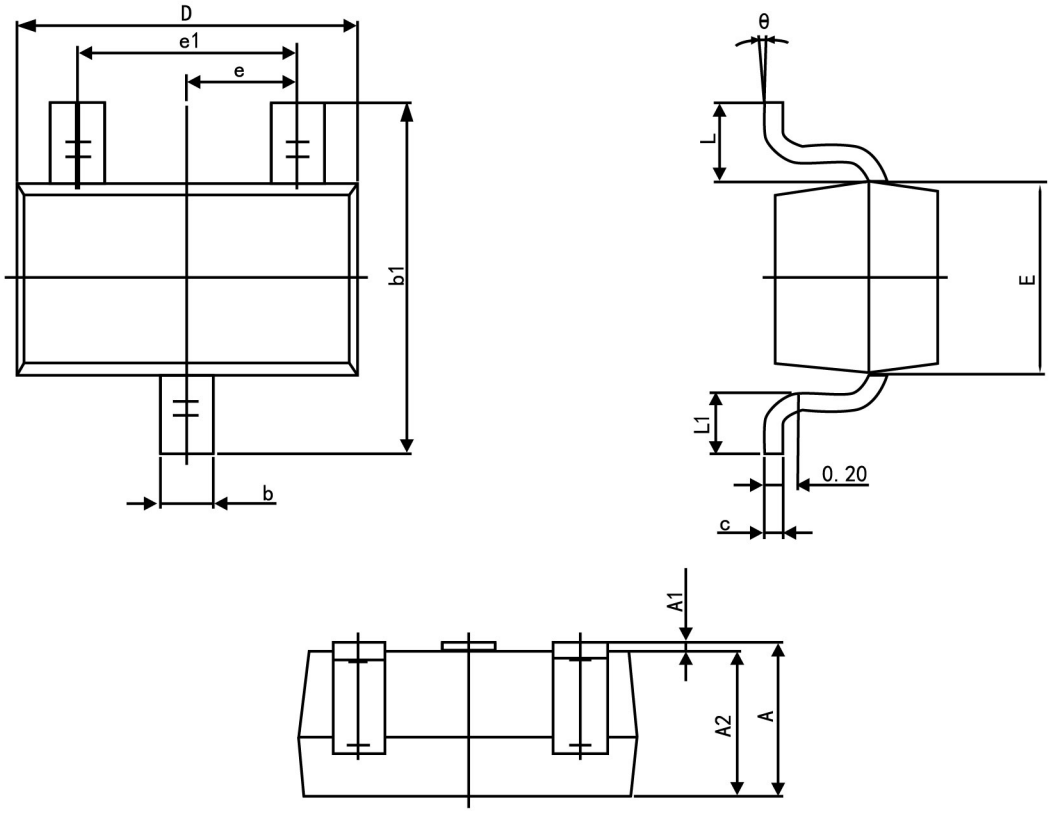


Bace-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



Current Gain Bandwidth Product

SOT-323 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.200	0.400
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
θ	**0°**	8°